

- Nominal Frequency

80.000MHz

L Pin 1 Connection

- Duty Cycle 50 ±5(%)

Tri-State (High Impedance)

EH25 45 ET T TS -80.000M

Series -RoHS Compliant (Pb-free) 5.0V 4 Pad 5mm x 7mm Ceramic SMD HCMOS/TTL High Frequency Oscillator

Frequency Tolerance/Stability ±50ppm Maximum

Operating Temperature Range --40°C to +85°C

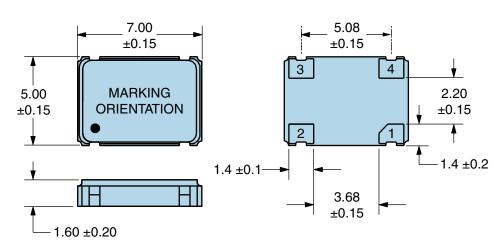
ELECTRICAL SPECIFICATIONS

Nominal Frequency	80.000MHz
Frequency Tolerance/Stability	±50ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°C, Shock, and Vibration)
Aging at 25°C	±5ppm/year Maximum
Operating Temperature Range	-40°C to +85°C
Supply Voltage	5.0Vdc ±10%
Input Current	50mA Maximum (No Load)
Output Voltage Logic High (Voh)	2.4Vdc Minimum with TTL Load, Vdd-0.4Vdc Minimum with HCMOS Load (IOH= -16mA)
Output Voltage Logic Low (Vol)	0.4Vdc Maximum with TTL Load, 0.5Vdc Maximum with HCMOS Load (IOH= +16mA)
Rise/Fall Time	4nSec Maximum (Measured at 0.8Vdc to 2.0Vdc with TTL Load; Measured at 20% to 80% of waveform with HCMOS Load)
Duty Cycle	50 \pm 5(%) (Measured at 50% of waveform with TTL Load or with HCMOS Load)
Load Drive Capability	5TTL Load or 15pF HCMOS Load Maximum
Output Logic Type	CMOS
Pin 1 Connection	Tri-State (High Impedance)
Tri-State Input Voltage (Vih and Vil)	+2.2Vdc Minimum to enable output, +0.8Vdc Maximum to disable output (High Impedance), No Connect to enable output.
Absolute Clock Jitter	±250pSec Maximum, ±100pSec Typical
One Sigma Clock Period Jitter	±50pSec Maximum, ±30pSec Typical
Start Up Time	10mSec Maximum
Storage Temperature Range	-55°C to +125°C

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

MIL-STD-883, Method 3015, Class 1, HBM: 1500V
MIL-STD-883, Method 1014, Condition A
UL94-V0
MIL-STD-883, Method 1014, Condition C
MIL-STD-883, Method 2002, Condition B
MIL-STD-883, Method 1004
J-STD-020, MSL 1
MIL-STD-202, Method 210, Condition K
MIL-STD-202, Method 215
MIL-STD-883, Method 2003
MIL-STD-883, Method 1010, Condition B
MIL-STD-883, Method 2007, Condition A

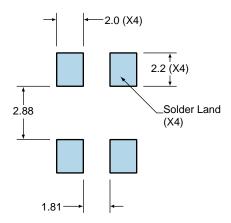
MECHANICAL DIMENSIONS (all dimensions in millimeters)



PIN	CONNECTION	
1	Tri-State	
2	Ground	
3	Output	
4	Supply Voltage	
LINE MARKING		
1	ECLIPTEK	
2	80.000M	
3	XXXXXX	

Suggested Solder Pad Layout

All Dimensions in Millimeters

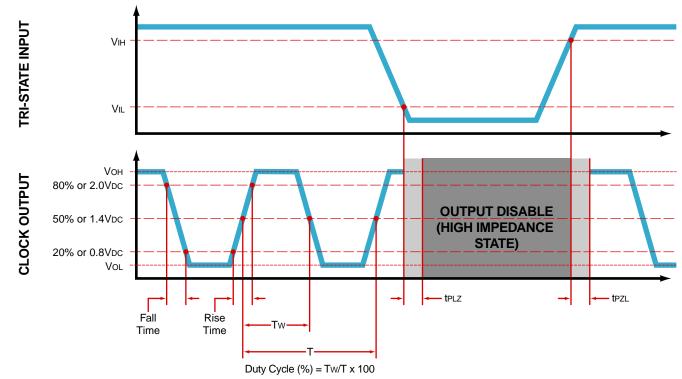


All Tolerances are ±0.1





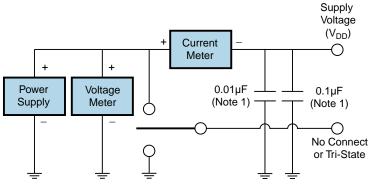
OUTPUT WAVEFORM & TIMING DIAGRAM

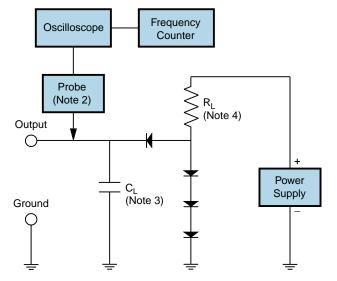


Test Circuit for TTL Output

Output Load Drive Capability	R _L Value (Ohms)	C _L Value (pF)
10TTL	390	15
5TTL	780	15
2TTL	1100	6
10LSTTL	2000	15
1TTL	2200	3







Note 1: An external 0.1µF low frequency tantalum bypass capacitor in parallel with a 0.01µF high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth

(>300MHz) passive probe is recommended.

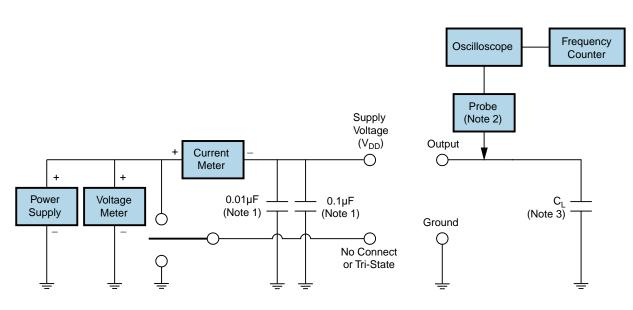
Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.

Note 4: Resistance value R_L is shown in Table 1. See applicable specification sheet for 'Load Drive Capability'.

Note 5: All diodes are MMBD7000, MMBD914, or equivalent.



Test Circuit for CMOS Output



Note 1: An external 0.1µF low frequency tantalum bypass capacitor in parallel with a 0.01µF high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

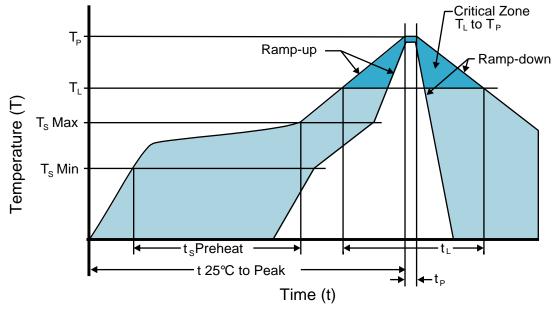
Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value \dot{C}_1 includes sum of all probe and fixture capacitance.



Recommended Solder Reflow Methods

EH2545ETTTS-80.000M



High Temperature Infrared/Convection

. .	
T _s MAX to T _L (Ramp-up Rate)	3°C/second Maximum
Preheat	
- Temperature Minimum (T _s MIN)	150°C
- Temperature Typical (T _s TYP)	175°C
 Temperature Maximum (T_s MAX) 	200°C
- Time (t _s MIN)	60 - 180 Seconds
Ramp-up Rate (T⊾ to T _P)	3°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	217°C
- Time (t∟)	60 - 150 Seconds
Peak Temperature (T _P)	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (T _P Target)	250°C +0/-5°C
Time within 5°C of actual peak (t _P)	20 - 40 seconds
Ramp-down Rate	6°C/second Maximum
Time 25°C to Peak Temperature (t)	8 minutes Maximum
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.



Recommended Solder Reflow Methods

EH2545ETTTS-80.000M



Low Temperature Infrared/Convection 240°C

T _s MAX to T _L (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum (T _s MIN)	N/A
 Temperature Typical (T_s TYP) 	150°C
 Temperature Maximum (T_s MAX) 	N/A
- Time (t _s MIN)	60 - 120 Seconds
Ramp-up Rate (T⊾ to T _P)	5°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	150°C
- Time (t∟)	200 Seconds Maximum
Peak Temperature (T _P)	240°C Maximum
Target Peak Temperature (T _P Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times
Time within 5°C of actual peak (t _P)	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)